

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

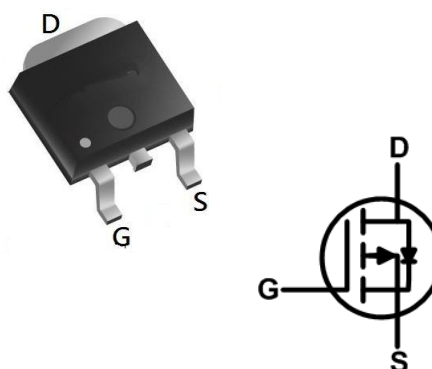
**Product Summary**

BVDSS	RDSON	ID
-30V	16mΩ	-40A

**Description**

The 40P03 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 40P03 meet the RoHS and Green Product requirement , 100% EAS guaranteed with full function reliability approved.

**TO252 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating		Units
		10s	Steady State	
V <sub>DS</sub>	Drain-Source Voltage	-30		V
V <sub>GS</sub>	Gate-Source Voltage	±20		V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-40		A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-25		A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-13.4	-8.5	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-10.7	-6.8	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-70		A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	72.2		mJ
I <sub>AS</sub>	Avalanche Current	-38		A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	34.7		W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	5	2	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150		°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150		°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s)	---	25	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	3.6	°C/W

**Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)**

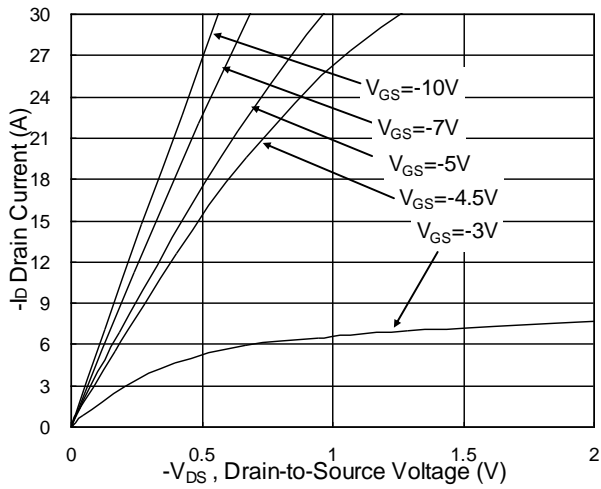
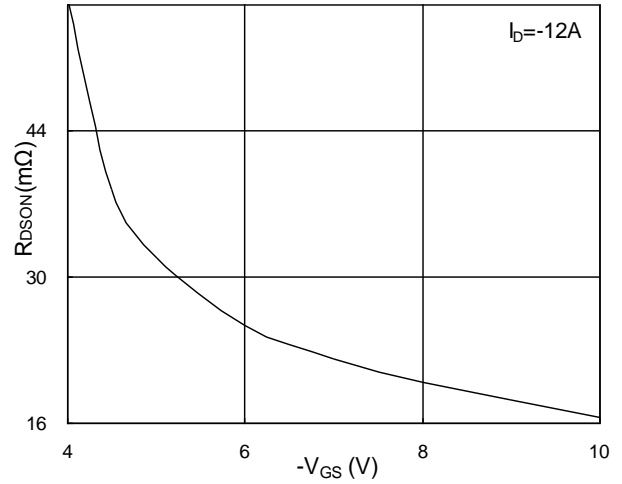
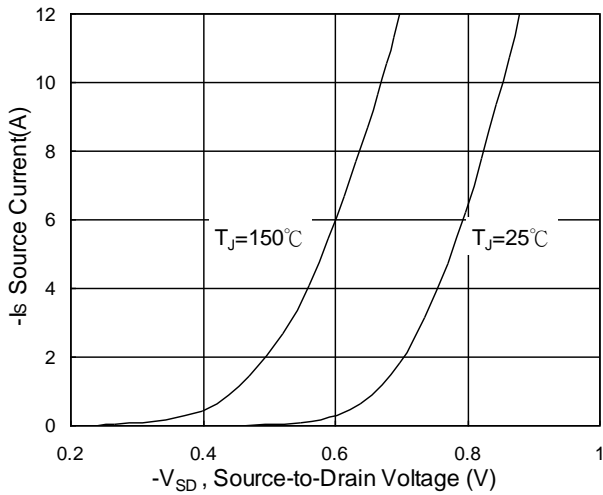
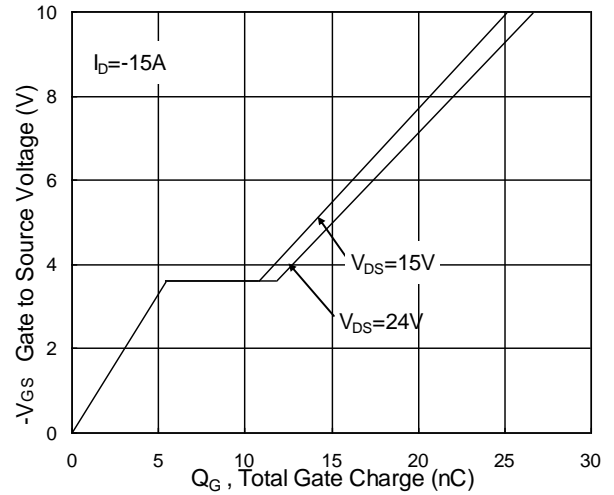
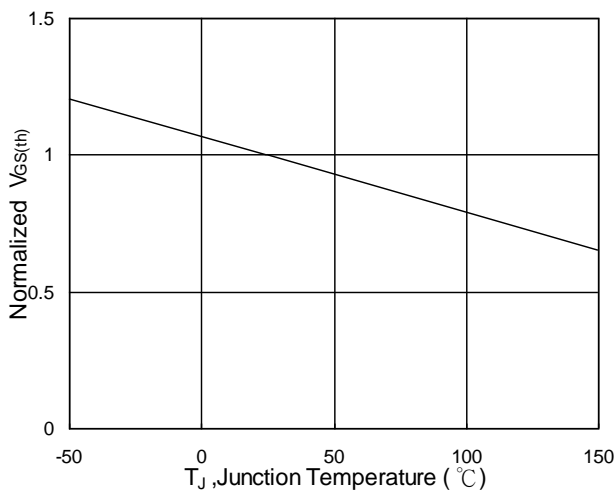
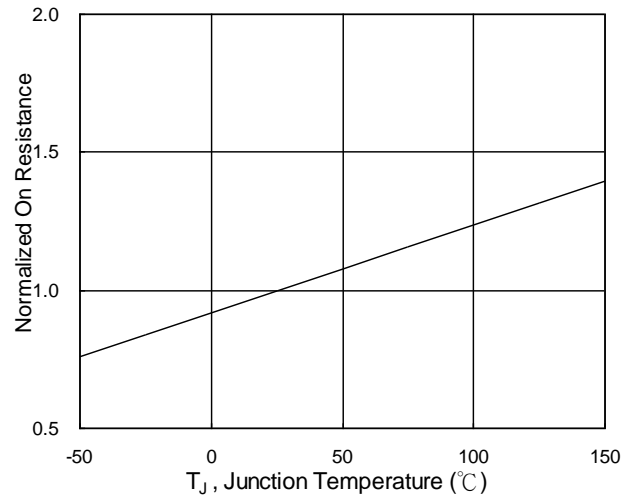
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$	---	-0.022	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=-10V, I_D=-15A$	---	16	20	m $\Omega$
		$V_{GS}=-4.5V, I_D=-10A$	---	20	25	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=-5V, I_D=-10A$	---	5	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	13	---	$\Omega$
$Q_g$	Total Gate Charge (-4.5V)	$V_{DS}=-15V, V_{GS}=-4.5V, I_D=-15A$	---	12.5	---	nC
$Q_{gs}$	Gate-Source Charge		---	5.4	---	
$Q_{gd}$	Gate-Drain Charge		---	5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-15A$	---	4.4	---	ns
$T_r$	Rise Time		---	11.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	34	---	
$T_f$	Fall Time		---	18	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	1345	---	pF
$C_{oss}$	Output Capacitance		---	194	---	
$C_{rss}$	Reverse Transfer Capacitance		---	158	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V$ , Force Current	---	---	-40	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	-75	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=-15A, di/dt=100A/\mu s$ ,	---	12.4	---	nS
$Q_{rr}$	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	5	---	nC

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is  $V_{DD}=-25V, V_{GS}=-10V, L=0.1\text{mH}, I_{AS}=-38A$
4. The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

**Typical Characteristics**

**Fig.1 Typical Output Characteristics**

**Fig.2 On-Resistance v.s Gate-Source**

**Fig.3 Forward Characteristics of Reverse**

**Fig.4 Gate-Charge Characteristics**

**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$** 

**Fig.6 Normalized  $R_{DS(ON)}$  v.s  $T_J$**

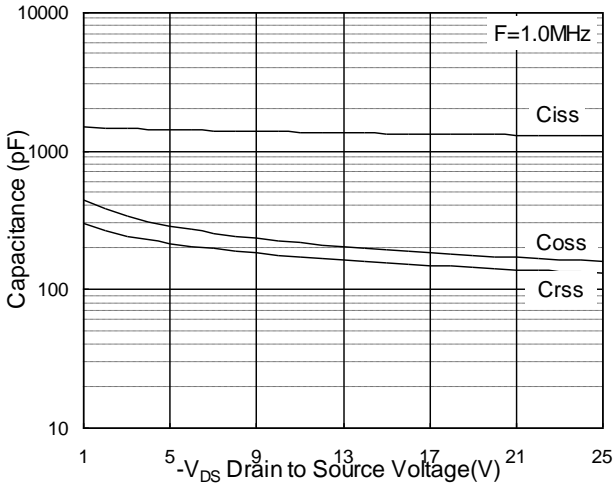


Fig.7 Capacitance

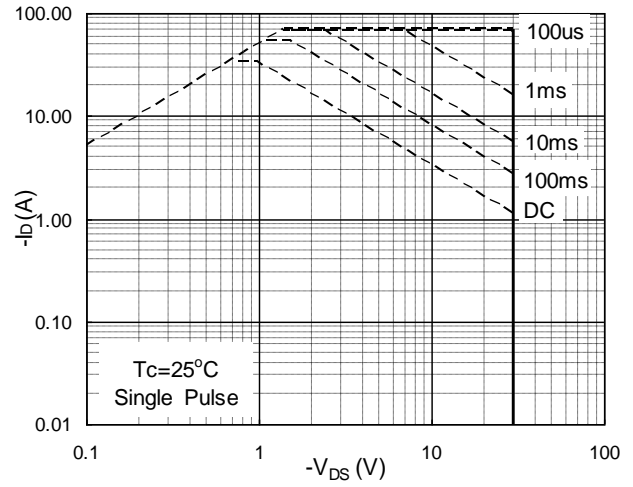


Fig.8 Safe Operating Area

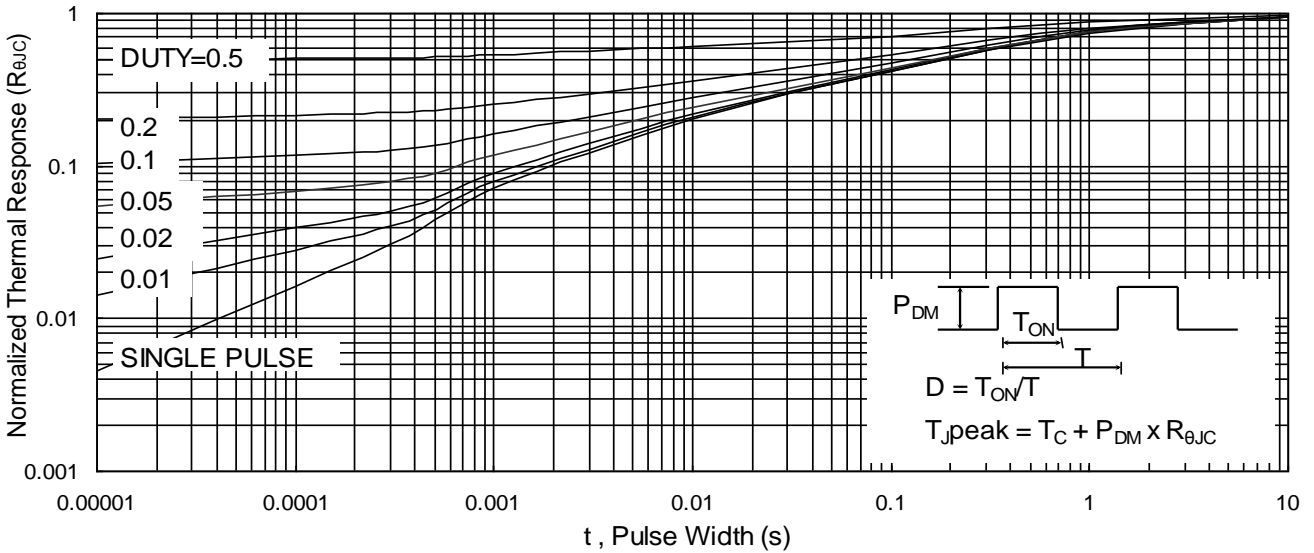


Fig.9 Normalized Maximum Transient Thermal Impedance

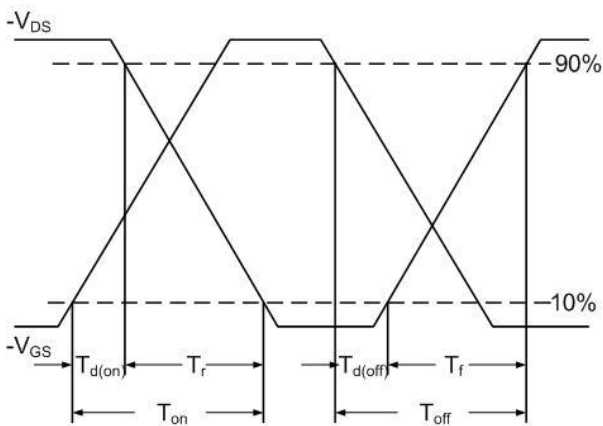


Fig.10 Switching Time Waveform

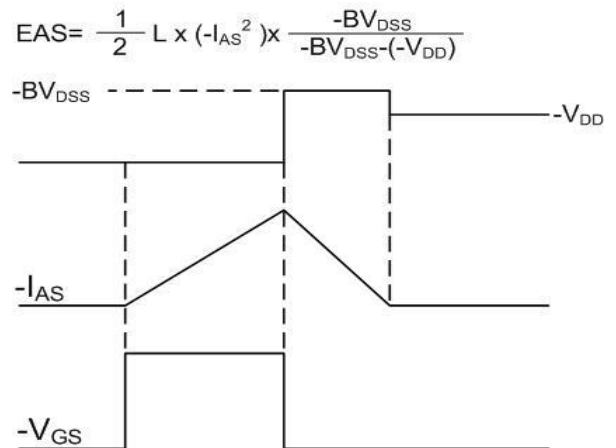


Fig.11 Unclamped Inductive Switching Waveform